

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT6087082

SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
CONVEYING PARTY DATA		
	Name	Execution Date
	UNITY SEMICONDUCTOR CORPORATION	05/04/2018
RECEIVING PARTY DATA		
Name:	HEFEI RELIANCE MEMORY LIMITED	
Street Address:	ROOM A-08, 14TH FLOOR, PLAZA A, BUILDING J1	
Internal Address:	INNOVATIVE INDUSTRIAL PARK PHASE II, HIGH-TECH ZONE	
City:	HEFEI	
State/Country:	CHINA	
PROPERTY NUMBERS Total: 1		
	Property Type	Number
	Application Number:	16864051
CORRESPONDENCE DATA		
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NAME OF SUBMITTER:	WEIGUO CHEN	
SIGNATURE:	/Weiguo Chen/	
DATE SIGNED:	04/30/2020	
Total Attachments: 3		
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ASSIGNMENT OF PATENT RIGHTS

Assignor: Unity Semiconductor Corporation
Address: 1050 Enterprise Way, Suite 700
Sunnyvale, CA 94089 USA

Assignee: Hefei Reliance Memory Limited
(with its Chinese name "合肥睿科微电子有限公司")
Address: Room A-08, 14th Floor, Plaza A, Building J1, Innovative Industrial Park
Phase II, High-tech Zone, Hefei, People's Republic of China

For good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, Unity Semiconductor Corporation ("Assignor"), a Delaware corporation, and Hefei Reliance Memory Limited (with its Chinese name "合肥睿科微电子有限公司") ("Assignee"), agree as follows:

Patents

"Patents" means the following patents and patent applications:

Patents Notable with Respect to RRAM RRAM有关专利清单

No.	Jarisdiction 地域	Patent/Publication/ Application # 专利号	App Title 应用名称
1	US	6972985	MEMORY ELEMENT HAVING ISLANDS
2	US	7082032	MULTI-RESISTIVE STATE ELEMENT WITH REACTIVE METAL
3	US	7394679	MULTI-RESISTIVE STATE ELEMENT WITH REACTIVE METAL
4	US	7538338	MEMORY USING VARIABLE TUNNEL BARRIER WIDTHS
5	US	7889539	MULTI-RESISTIVE STATE MEMORY DEVICE WITH CONDUCTIVE OXIDE ELECTRODES
6	US	8062942	METHOD FOR FABRICATING MULTI-RESISTIVE STATE MEMORY DEVICES
7	US	8237142	CONTINUOUS PLANE OF THIN-FILM MATERIALS FOR A TWO-TERMINAL CROSS-POINT MEMORY
8	US	8274817	NON VOLATILE MEMORY DEVICE ION BARRIER
9	US	8339867	FUSE ELEMENTS BASED ON TWO-TERMINAL RE-WRITEABLE NON-VOLATILE MEMORY
10	US	8395928	THRESHOLD DEVICE FOR A MEMORY ARRAY
11	US	8610099	PLANAR RESISTIVE MEMORY INTEGRATION
12	US	8611130	METHOD FOR FABRICATING MULTI-RESISTIVE STATE MEMORY DEVICES
13	US	8675389	MEMORY ELEMENT WITH A REACTIVE METAL LAYER
14	US	9029827	PLANAR RESISTIVE MEMORY INTEGRATION
15	US	9058300	INTEGRATED CIRCUITS AND METHODS TO CONTROL ACCESS TO MULTIPLE LAYERS OF MEMORY
18	US	9159408	MEMORY ELEMENT WITH A REACTIVE METAL LAYER
19	US	9159913	TWO-TERMINAL REVERSIBLY SWITCHABLE MEMORY DEVICE
24	US	9484533	MULTI-LAYERED CONDUCTIVE METAL OXIDE STRUCTURES AND METHODS FOR FACILITATING ENHANCED PERFORMANCE CHARACTERISTICS OF TWO-TERMINAL MEMORY CELLS

No.	Jurisdiction 地域	Patent/Publication/ Application # 专利号	App Title 应用名称
29	US	9570515	MEMORY ELEMENT WITH A REACTIVE METAL LAYER
30	US	9806130	MEMORY ELEMENT WITH A REACTIVE METAL LAYER
32	US	9818799	MULTI-LAYERED CONDUCTIVE METAL OXIDE STRUCTURES AND METHODS FOR FACILITATING ENHANCED PERFORMANCE CHARACTERISTICS OF TWO-TERMINAL MEMORY CELLS
34	US	9831425	TWO-TERMINAL REVERSIBLY SWITCHABLE MEMORY DEVICE
37	CN	ZL200580038024.5	MEMORY ELEMENT AND METHOD FOR CREATING MEMORY EFFECT
41	US	2018-0122857	MEMORY ELEMENT WITH A REACTIVE METAL LAYER
46	US	15/797,452	TWO-TERMINAL REVERSIBLY SWITCHABLE MEMORY DEVICE
47	US	15/811,179	MULTI-LAYERED CONDUCTIVE METAL OXIDE STRUCTURES AND METHODS FOR FACILITATING ENHANCED PERFORMANCE CHARACTERISTICS OF TWO-TERMINAL MEMORY CELLS

Assignment

Effective May 4, 2018, Assignor hereby irrevocably assigns, transfers, and conveys to Assignee all of its right, title, and interest in and to the Patents, and all of its rights, claims, and privileges pertaining to, arising out of, or associated with, the Patents, including, without limitation, the right to the underlying inventions, the right to file, prosecute and maintain the Patents, and the right to sue, seek equitable relief, and recover damages for past, present, and future infringement thereof.

Further Assignment

Assignor further assigns to and empowers Assignee, its successors, assigns, or nominees, all rights to make applications for patents or other forms of protection for said inventions and to prosecute such applications and the Patents.

Assignor's representative signing below represents that he or she is duly authorized to sign documents on behalf of Assignor.

Assignor grants Assignee or its agents the power to insert on this Assignment any further identification that may be necessary or desirable to in order to comply with the rules of the United States Patent and Trademark Office for recordation of this document.

EXECUTED this 18th day of June, 2018.

UNITY SEMICONDUCTOR CORPORATION

Signed 

Typed Name: J. Kim

Title: SVP / Director

HEFEI RELIANCE MEMORY LIMITED

(with its Chinese name "合肥睿科微电子有限公司")

Signed 

Typed Name: Zhichao Lu

Title: CEO